

METHODS FOR FABRICATING METAL-OXIDE-SEMICONDUCTOR FIELD EFFECT TRANSISTORS USING GATE SIDEWALL SPACERS

Abstract of the Disclosure

5 Metal-Oxide-Semiconductor Field Effect Transistor (MOSFET) is
fabricated by forming gate spacers on both sidewalls of a gate pattern in a
semiconductor substrate including first and second regions. Then, a first impurity
region is formed in the semiconductor substrate at the first region, and the gate
spacer exposed at the first region is removed. A second impurity region is formed
10 in the semiconductor substrate at the first region. A third impurity region is
formed at the semiconductor substrate in the second region, and the gate spacer
exposed at the second region is removed. A fourth impurity region is formed in the
semiconductor substrate at the second region. The first and third impurity regions
are formed deeper than the second and fourth impurity regions.